

# MGSF1N02LT1

## Power MOSFET 750 mAmps, 20 Volts N-Channel SOT-23

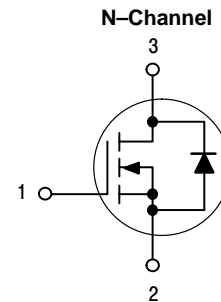
These miniature surface mount MOSFETs low  $R_{DS(on)}$  assure minimal power loss and conserve energy, making these devices ideal for use in space sensitive power management circuitry. Typical applications are dc-dc converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low  $R_{DS(on)}$
- Miniature SOT-23 Surface Mount Package Saves Board Space

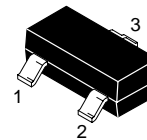
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	20	Vdc
Gate-to-Source Voltage – Continuous	$V_{GS}$	$\pm 20$	Vdc
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$ – Pulsed Drain Current ( $t_p \leq 10 \mu\text{s}$ )	$I_D$ $I_{DM}$	750 2000	mA
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	400	mW
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	300	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	$T_L$	260	$^\circ\text{C}$

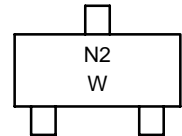
750 mAmps  
20 VOLTS  
 $R_{DS(on)} = 90 \text{ m}\Omega$



### MARKING DIAGRAM

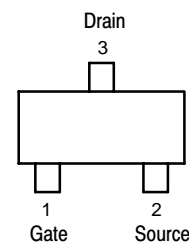


SOT-23  
CASE 318  
STYLE 21



W = Work Week

### PIN ASSIGNMENT



### ORDERING INFORMATION

Device	Package	Shipping
MGSF1N02LT1	SOT-23	3000 Tape & Reel
MGSF1N02LT3	SOT-23	10,000 Tape & Reel

**Preferred** devices are recommended choices for future use and best overall value.

# MGSF1N02LT1

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 10 μAdc)	V <sub>(BR)DSS</sub>	20	–	–	Vdc
Zero Gate Voltage Drain Current (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 Vdc) (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	I <sub>DSS</sub>	–	–	1.0 10	μAdc
Gate-Body Leakage Current (V <sub>GS</sub> = ± 20 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	–	–	±100	nAdc

### ON CHARACTERISTICS (Note 1.)

Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μAdc)	V <sub>GS(th)</sub>	1.0	1.7	2.4	Vdc
Static Drain-to-Source On-Resistance (V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 1.2 Adc) (V <sub>GS</sub> = 4.5 Vdc, I <sub>D</sub> = 1.0 Adc)	r <sub>DS(on)</sub>	–	0.075 0.115	0.090 0.130	Ohms

### DYNAMIC CHARACTERISTICS

Input Capacitance	(V <sub>DS</sub> = 5.0 Vdc)	C <sub>iss</sub>	–	125	–	pF
Output Capacitance	(V <sub>DS</sub> = 5.0 Vdc)	C <sub>oss</sub>	–	120	–	
Transfer Capacitance	(V <sub>DG</sub> = 5.0 Vdc)	C <sub>rss</sub>	–	45	–	

### SWITCHING CHARACTERISTICS (Note 2.)

Turn-On Delay Time	(V <sub>DD</sub> = 15 Vdc, I <sub>D</sub> = 1.0 Adc, R <sub>L</sub> = 50 Ω)	t <sub>d(on)</sub>	–	2.5	–	ns
Rise Time		t <sub>r</sub>	–	1.0	–	
Turn-Off Delay Time		t <sub>d(off)</sub>	–	16	–	
Fall Time		t <sub>f</sub>	–	8.0	–	
Gate Charge (See Figure 6)		Q <sub>T</sub>	–	6000	–	pC

### SOURCE-DRAIN DIODE CHARACTERISTICS

Continuous Current	I <sub>S</sub>	–	–	0.6	A
Pulsed Current	I <sub>SM</sub>	–	–	0.75	
Forward Voltage (Note 2.)	V <sub>SD</sub>	–	0.8	–	V

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.